#### IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:

HATAKEYAMA, Jun et al

Appl. No.:

NEW

Group:

Filed:

January 29, 2004

Examiner:

For:

POLYMER, RESIST COMPOSITION AND

PATTERNING PROCESS

INFORMATION DISCLOSURE STATEMENT (SUBMISSION CONCURRENT WITH THE FILING OF A NEW PATENT APPLICATION)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

January 29, 2004

#### Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

# I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications, or other information submitted for consideration by the Office are listed on PTO-1449, attached hereto.

## II. COPIES

- a. This application was filed before June 30, 2003.

  Accordingly, submitted herewith is a legible copy of (i) each U.S. and foreign patent; (ii) each publication or that portion which caused it to be listed; and (iii) all other information or that portion which caused it to be listed.
- b. Main this application was filed on or after June 30, 2003. Accordingly, copies of cited US patents and patent application publications therefore are not included. Copies of foreign patent documents and non-patent literature are included.

c. This application is a National Phase of a PCT application. Some or all of the documents listed on the PTO-1449 are not enclosed because they were cited in the International Search Report and copies should be forwarded from the International Search Authority. If copies are needed, please contact the undersigned.

# III. CONCISE EXPLANATION OF THE RELEVANCE (check at least one box)

#### a. DOCUMENTS IN THE ENGLISH LANGUAGE

The patents, publications, or other information listed on the attached PTO 1449 are in the English language and therefore, do not require a statement of relevancy.

### b. DOCUMENTS NOT IN THE ENGLISH LANGUAGE

A concise explanation of the relevance of all patents, publications, or other information listed that is not in the English language is as follows:

The relevancy of the Japanese language documents can be determined from a review of the English language Abstracts attached thereto.

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An English language version of the search report or action that indicates the degree of relevance found by the foreign office is attached, thereby satisfying the requirement for a concise explanation. See MPEP 609(III)(A)(3).

#### d. 🛛 **OTHER**

The following additional information is provided for the Examiner's consideration.

JP 2001-158808 corrsponds to US Patent No. 6,492,089.

#### <u>FEES</u>

This Information Disclosure Statement is being filed concurrently with the filing of a new patent application; therefore, no fee is required.

If the Examiner has any questions concerning this IDS, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule and charge the appropriate fee to Deposit Account No. 02-2448.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under § 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

GMM/smt 0171-1058P Falls Church, VA 22040-0747 (703) 205-8000

Attachment(s): ✓⊠	Form PTO-1449(s)
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	Foreign Search Report
	Fee
	Other:

(Rev. 09/30/03)

Form PTO-1449				0171-1058P	APPLICATION NO. NEW				
INFORMATION DISCLOSURE CITATION IN AN APPLICATION			HATAKEYAMA, Jun et al						
(Use several sheets if necessary)			FILING DATE January 29, 2004  GROUP						
			U	.S. PATENT D	OCUMENTS		·		
EXAMINER INITIAL	DOCUMENT NUMBER		Kind	DATE	NAME CLASS		SUB FILING DATE CLASS IF APPROPRIATE		
	115	4,491,628		1985-01-01	Ito et al.		<u> </u>		
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		2003/0224291	A1	2003-12-4	Hatakeyama et al.			<del>                                     </del>	
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	1		FOR	EIGN PATENT	DOCUMENTS	<u> </u>		<u> </u>	
	Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSI	LATION NO
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	JP	63-27829	A	1988-02-05	JAPAN			ABS	
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Schmaljohann et al., Fundamental Studies of Fluoropolymer Photoresists for 157 nm Lithography, J. Photopolymer Sci. and Technol., Vol. 13, No. 3 (2000) pp. 451-458									
EXAMINE	R			DAT	E CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									

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